

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (currently amended): A method for reducing thickness of spin-on glass on semiconductor wafers, the method comprising:

forming a spin-on glass layer on a semiconductor wafer wherein said spin-on glass layer comprises a protuberance at an outer edge of said semiconductor wafer;

rotatably mounting a said semiconductor wafer;

positioning a grinding member proximate an said outer edge of the semiconductor wafer;

rotating the semiconductor wafer;

rotating the grinding member;

applying a chemical to the spin-on glass protuberance at said outer edge of said semiconductor wafer; and

engaging the rotating grinding member with the spin-on glass protuberance at said outer edge of the rotating semiconductor wafer.

Claim 2 (original): The method of Claim 1, further comprising:

disengaging the rotating grinding member; and

rinsing the semiconductor wafer with deionized water.

Claim 3 (original): The method of Claim 1, wherein rotatably mounting the semiconductor wafer comprises securing the semiconductor wafer in a substantially horizontal position to a spindle with a vacuum chuck.

Claim 4 (original): The method of Claim 1, wherein positioning the grinding member comprises orientating the grinding member in a substantially horizontal position.

Claim 5 (original): The method of Claim 1, wherein positioning the grinding member comprises orientating the grinding member in a substantially vertical position.

Claim 6 (original): The method of Claim 1, wherein applying the chemical comprises using a syringe to apply a hydrofluoric acid to approximately a portion of the outer edge that is engaged with the grinding member.

Claim 7 (original): The method of Claim 1, wherein engaging the rotating grinding member with the outer edge of the rotating semiconductor wafer comprises pneumatically controlling the grinding member.

Claim 8 (original): The method of Claim 1, wherein engaging the rotating grinding member with the outer edge of the rotating semiconductor wafer comprises spring-loading the grinding member.

Claims 9-14 (canceled)

Claim 15 (currently amended): A method for reducing thickness of spin-on glass on semiconductor wafers, the method comprising:

providing a chemical in a container;

forming a spin-on glass layer on a semiconductor wafer wherein said spin-on glass layer comprises a protuberance at an outer edge of said semiconductor wafer;

rotatably mounting a said semiconductor wafer;

bearing a grinding member against a portion of an said spin-on glass protuberance at said outer edge of the semiconductor wafer; and

rotating the semiconductor wafer while the semiconductor wafer is in contact with the grinding member and while the portion of said spin-on glass

protuberance at the outer edge of the semiconductor wafer is immersed in the chemical.

Claim 16 (original): The method of Claim 15, further comprising rinsing the semiconductor wafer with deionized water.

Claim 17 (original): The method of Claim 15, wherein rotatably mounting the semiconductor wafer comprises securing the semiconductor wafer in a substantially vertical position to a spindle with a vacuum chuck.

Claim 18 (original): The method of Claim 15, wherein positioning the grinding member comprises orientating the grinding member in a substantially horizontal position.

Claim 19 (original): The method of Claim 15, wherein bearing the grinding member against the portion of the outer edge comprises pneumatically controlling the grinding member.

Claim 20 (original): The method of Claim 15, wherein bearing the grinding member against the portion of the outer edge comprises spring-loading the grinding member.

Amendments to the Drawings:

None